

**Notice of References Cited**Application/Control No.  
**08/903,453**Applicant(s)/Patent Under Reexam  
**Forbes et al.**Examiner  
**George C. Eckert II**Art Unit  
**2815**

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**U.S. PATENT DOCUMENTS**

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Name	Classification <sup>2</sup>
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**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Capasso et al., New Floating-Gate AlGaAs/GaAs Memory Devices with Graded-Gap Electron Injector and Long Retention Times, August 1988, IEEE, Electron Device Letters, Vol. 9, No. 8, pp. 377-79.
V	Burns et al., Principles of Electronic Circuits, 1987, West Publishing, p. 380.
W	Ng, Complete Guide to Semiconductor Devices, 1995, McGraw Hill, pp. 322-28, 605-08.
X	Wolf, Silicon Processing for the VLSI Era, Volume 2: Process Integration, 1990, Lattice Press, pp. 623-28.

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